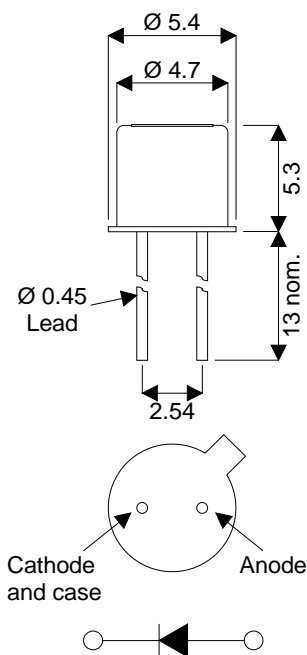


MECHANICAL DATA

Dimensions in mm.



TO-18 Package

Pin 1 – Anode

Pin 2 – Cathode & Case

P.I.N. PHOTODIODE

FEATURES

- EXCELLENT LINEARITY
- LOW NOISE
- WIDE SPECTRAL RESPONSE
- WIDE INTRINSIC BANDWIDTH
- LOW LEAKAGE CURRENT
- LOW CAPACITANCE
- INTEGRAL OPTICAL FILTER OPTION **note 1**
- TO18 HERMETIC METAL CAN PACKAGE
- EMI SCREENING MESH AVAILABLE

Note 1 Contact Semelab Plc for filter options

DESCRIPTION

The SMP400G-BD is a Silicon P.I.N. photodiode incorporated in a compact, hermetic metal can package. The electrical terminations are via two leads of diameter 0.005" on a pitch of 0.1". The taller can structure affords a greater range of optical filter options. The cathode of the photodiode is electrically connected to the package.

The photodiode structure has been optimised for high sensitivity, high speed light measurement applications. The moderate viewing angle facilitates easy alignment of the device with on-axis illumination sources. The metal can and optional screening mesh ensure a rugged device with a high degree of immunity to radiated electrical interference.

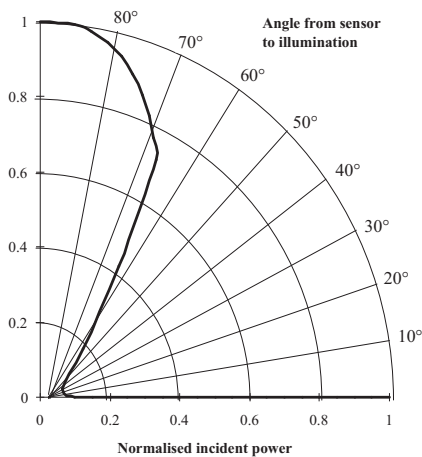
ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

Operating temperature range	-40°C to +70°C
Storage temperature range	-45°C to +80°C
Temperature coefficient of responsivity	0.35% per °C
Temperature coefficient of dark current	x2 per 8°C rise
Reverse breakdown voltage	60V

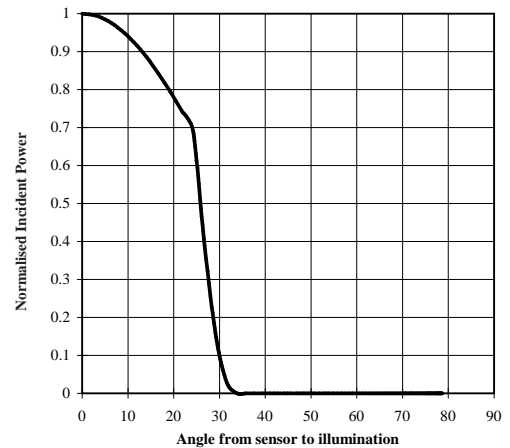
CHARACTERISTICS (T_{amb}=25°C unless otherwise stated)

Characteristic	Test Conditions.	Min.	Typ.	Max.	Units
Responsivity	λ at 900nm	0.45	0.55		A/W
Active Area			0.62		mm ²
Dark Current	E = 0 Dark 1V Reverse		0.1	1.0	nA
	E = 0 Dark 10V Reverse		0.5	2.5	
Breakdown Voltage	E = 0 Dark 10 μ A Reverse	60	80		V
Capacitance	E = 0 Dark 0V Reverse		8	12	pF
	E = 0 Dark 20V Reverse		1.5	2.5	
Rise Time	30V Reverse 50 Ω		4		ns
NEP	900nm		7.2	0.45	W/ \sqrt Hz

Directional characteristics



Directional Characteristics



Spectral Response

